

| Ref # | Hits    | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|---------|---|---|------------------|---------|------------------|
| L2    | 28      | ((("5963810") or ("6027976") or ("20020197790") or ("20030045080") or ("20020197790") or ("6514828") or ("6436777") or ("20030045080") or ("6544906") or ("6184072") or ("6420279") or ("20030032303") or ("5783478") or ("6625217") or ("6306742") or ("5891798")).PN. | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/01/04 15:59 |
| L3    | 6       | 2 and (high k gate dielectric)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2005/01/04 16:02 |
| L4    | 1462619 | semiconductor   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2005/01/04 16:02 |
| L5    | 5       | 4 and ((high k gate dielectric) with substrate) and ((wet chemical treatment) with impurit\$4 with oxygen)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2005/01/04 16:19 |
| L6    | 5       | 4 and (high k gate dielectric) and ((wet chemical treatment) with impurit\$4 with oxygen)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2005/01/04 16:20 |
| L7    | 5       | 4 and (high k gate dielectric) and (wet chemical treatment) and impurit\$4 and oxygen   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2005/01/04 16:21 |
| L8    | 14      | 4 and (high k gate dielectric) and (wet chemical) and impurit\$4 and oxygen   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2005/01/04 16:22 |